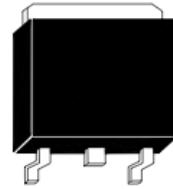
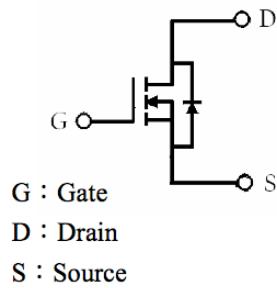


**MSD50N03**
**TO-252**
**N-Channel Logic Level Enhancement  
Mode Power MOSFET**
**FEATURES**

- V<sub>DS</sub>=30V, I<sub>D</sub>=50A, R<sub>DSON</sub>=9mΩ
- Low Gate Charge
- Repetitive Avalanche Rated
- Simple Drive Requirement
- Fast Switching Characteristic
- RoHS compliant package

|                         |     |
|-------------------------|-----|
| <b>BV<sub>DSS</sub></b> | 30V |
| <b>I<sub>D</sub></b>    | 50A |
| <b>R<sub>DSON</sub></b> | 9mΩ |


**G D S**

**Absolute Maximum Ratings** (T<sub>c</sub>=25°C unless otherwise noted)

| Parameter  | Symbol                            | Value    | Unit |
|--|-----------------------------------|----------|------|
| Drain-Source Voltage   | V <sub>DS</sub>                   | 30       | V    |
| Gate-Source Voltage  | V <sub>GS</sub>                   | ±20      | V    |
| Continuous Drain Current @ T <sub>C</sub> =25°C                        | I <sub>D</sub>                    | 50       | A    |
| Continuous Drain Current @ T <sub>C</sub> =100°C                       | I <sub>D</sub>                    | 35       | A    |
| Pulsed Drain Current   | I <sub>DM</sub> *1                | 140      | A    |
| Avalanche Current  | I <sub>AS</sub>                   | 37.5     | A    |
| Avalanche Energy @ L=0.1mH, I <sub>D</sub> =37.5A, R <sub>g</sub> =25Ω | E <sub>AS</sub>                   | 70       | mJ   |
| Repetitive Avalanche Energy @ L=0.05mH                                 | E <sub>AR</sub> *2                | 15       | mJ   |
| Power Dissipation (T <sub>C</sub> =25°C)                               | PD                                | 60       | W    |
| Power Dissipation (T <sub>C</sub> =100°C)                              |                                   | 32       | W    |
| Operating Junction and Storage Temperature                             | T <sub>j</sub> , T <sub>stg</sub> | -55~+175 | °C   |

Note:

 100% UIS testing in condition of V<sub>D</sub>=15V, L=0.1mH, V<sub>G</sub>=10V, I<sub>L</sub>=25A, Rated V<sub>DS</sub>=25V N-CH

\*1. Pulse width limited by maximum junction temperature

\*2. Duty cycle≤1%

**Thermal characteristics** (T<sub>c</sub>=25°C unless otherwise noted)

| Parameter                  | Symbol            | Value | Unit |
|----------------------------|-------------------|-------|------|
| Typical thermal resistance | R <sub>thjc</sub> | 2.5   | °C/W |
|                            | R <sub>θJA</sub>  | 75    |      |

**Characteristics (T<sub>c</sub>=25°C, unless otherwise specified)**

| Symbol                        | Test Conditions                         | Min. | Typ. | Max. | Unit |
|-------------------------------|---|------|------|------|------|
| <b>Static Characteristics</b> |   |      |      |      |      |
| BVDSS                         | VGS=0, ID=250μA                         | 30   | -    | -    | V    |
| VGS                           | VDS = VGS, ID=250μA                     | 1.0  | 1.7  | 3.0  | V    |
| GFS                           | VDS =5V, ID=20A                         | -    | 20   | -    | S    |
| IGSS                          | VGS=±20                                 | -    | -    | ±100 | nA   |
| IDSS                          | VDS =24V, VGS =0                        | -    | -    | 1    | uA   |
|                               | VDS =20V, VGS =0, T <sub>j</sub> =125°C | -    | -    | 25   |      |
| ID(ON)                        | VGS =10V, VDS=10V                       | 50   | -    | -    | A    |
| *RDS(ON)                      | VGS =10V, ID=25A                        | -    | 7.5  | 9    | mΩ   |
|                               | VGS =5V, ID=20A                         | -    | 12   | 15   |      |

**Dynamic Characteristics**

|                          |   |   |      |   |    |
|--------------------------|---|---|------|---|----|
| R <sub>g</sub>           | VGS=15mV, VDS=0, f=1MHz                       | - | 1.7  | - | Ω  |
| Q <sub>g</sub> (VGS=10V) | ID=25A, VDS=15V, VGS=10V                      | - | 23   | - | nC |
| Q <sub>g</sub> (VGS=5V)  |   | - | 13   | - |    |
| Q <sub>gs</sub>          |   | - | 4.7  | - |    |
| Q <sub>gd</sub>          |   | - | 7.4  | - |    |
| t <sub>d</sub> (ON)      | VDS=15V, ID=25A, VGS=10V,<br>RG=2.7Ω, RD=0.6Ω | - | 10   | - | ns |
| t <sub>r</sub>           |   | - | 8    | - |    |
| t <sub>d</sub> (OFF)     |   | - | 30   | - |    |
| t <sub>f</sub>           |   | - | 5    | - |    |
| C <sub>iss</sub>         | VGS=0V, VDS=15V, f=1MHz                       | - | 2020 | - | pF |
| C <sub>oss</sub>         |   | - | 275  | - |    |
| C <sub>rss</sub>         |   | - | 160  | - |    |

**Source-Drain Diode Characteristics**

|                 |  |   |     |     |    |
|-----------------|--|---|-----|-----|----|
| I <sub>S</sub>  |  | - | -   | 50  | A  |
| I <sub>SM</sub> |  | - | -   | 140 |    |
| V <sub>SD</sub> | I <sub>F</sub> =I <sub>S</sub> , VGS=0                       | - | -   | 1.3 | V  |
| t <sub>rr</sub> | I <sub>F</sub> =I <sub>S</sub> , dI <sub>F</sub> /dt=100A/μs | - | 22  | -   | nS |
| IRM(REC)        |  | - | 180 | -   | A  |
| Q <sub>rr</sub> |  | - | 12  | -   | nC |

\*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

**Ordering Information**

|         |                        |
|---------|------------------------|
| Package | Shipping               |
| TO-252  | 2500 pcs / Tape & Reel |